

### 30V P-Channel MOSFET



**SOT-26** 

#### Pin Definition:

1. Drain

6. Drain

2. Drain

5. Drain

3. Gate

4. Source

#### **Key Parameter Performance**

Parameter		Value	Unit	
$V_{DS}$		-30	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = -10V	60	mΩ	
	$V_{GS} = -4.5V$	100		
$Q_g$		9.52	nC	

#### **Features**

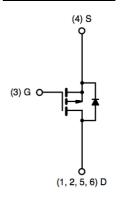
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

#### **Ordering Information**

Part No.	Package	Packing
TSM3457CX6 RFG	SOT-26	3kpcs / 7" Reel

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

#### **Block Diagram**



P-Channel MOSFET

#### **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current		I <sub>D</sub>	-5	Α
Pulsed Drain Current		I <sub>DM</sub>	-20	Α
Continuous Source Current (Diode Conductio	n) <sup>(Note 1,2)</sup>	I <sub>S</sub>	-1.7	Α
Maximum Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2.0	W
	T <sub>A</sub> =70°C		1.3	
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature	Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R_{ ext{ hetaJC}}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\Theta JA}$	80	°C/W

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**Electrical Specifications** (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV <sub>DSS</sub>	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V <sub>GS(TH)</sub>	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	μΑ
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -10V$	I <sub>D(ON)</sub>	-20			Α
Proin Course On Chata Provintence	$V_{GS} = -4.5V$ , $I_{D} = -3.7A$			82	100	mΩ
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -5A$	R <sub>DS(ON)</sub>		50	60	
Forward Transconductance	$V_{DS} = -15V, I_{D} = -5A$	<b>g</b> fs		10		S
Diode Forward Voltage	$I_S = -1.7A, V_{GS} = 0V$	V <sub>SD</sub>		-0.8	-1.2	V
Dynamic (Note 4,5)						
Total Gate Charge		Qg		9.52		
Gate-Source Charge	$V_{DS} = -15V, I_D = -3.7A,$ $V_{GS} = -10V$	$Q_gs$		3.43		nC
Gate-Drain Charge		$Q_{gd}$		1.71		
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>iss</sub>		551.57		
Output Capacitance		C <sub>oss</sub>		90.96		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		60.79		
Switching (Note 4,5)						
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega,$ $I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	t <sub>d(on)</sub>		10.8		
Turn-On Rise Time		t <sub>r</sub>	-	2.33		
Turn-Off Delay Time		t <sub>d(off)</sub>	-	22.53		ns
Turn-Off Fall Time		t <sub>f</sub>		3.87		

#### Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board,  $t \le 5$  sec.
- 3. pulse test: PW  $\leq$  300 $\mu$ S, duty cycle  $\leq$  2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

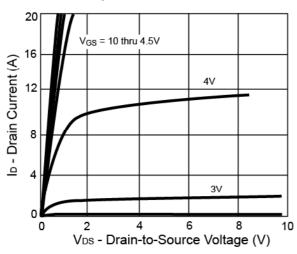


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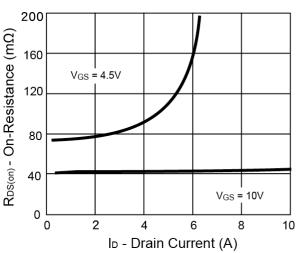


#### **Electrical Characteristics Curves**

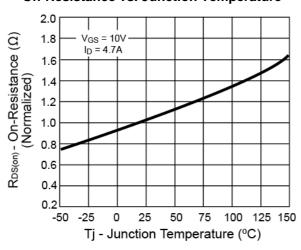
#### **Output Characteristics**



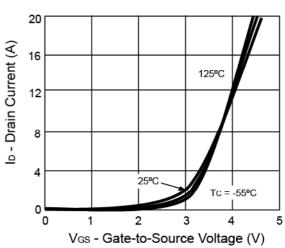
**On-Resistance vs. Drain Current** 



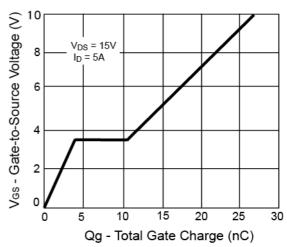
**On-Resistance vs. Junction Temperature** 



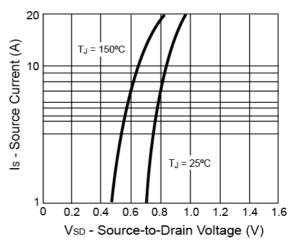
**Transfer Characteristics** 



**Gate Charge** 



**Source-Drain Diode Forward Voltage** 



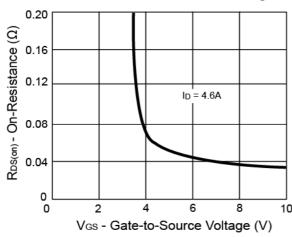


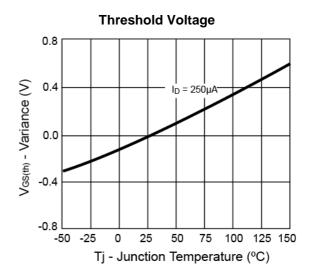
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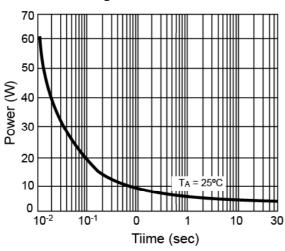
#### **Electrical Characteristics Curves**

#### On-Resistance vs. Gate-Source Voltage

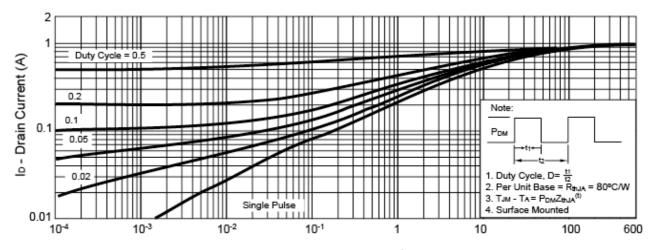




#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

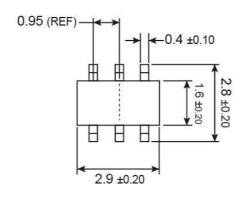


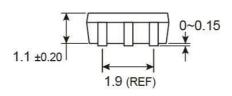
Square Wave Pulse Duration (sec)

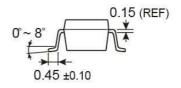




# **SOT-26 Mechanical Drawing**







Unit: Millimeters

### **Marking Diagram**



57 = Device Code

Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan **P** =Feb **Q** =Mar R = Apr**S** =May **T** =Jun

**W** =Sep X =Oct Y =Nov Z =Dec

**U** =Jul

V =Aug

L = Lot Code



## TSM3457 30V P-Channel MOSFET

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